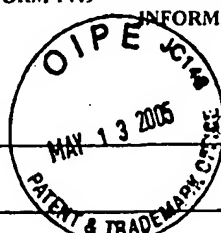


FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 3165.41USU1	Application Number: 10/723,382
	Applicant: MUNNS	
	Filing Date: 11/25/2003	Group Art Unit: 2815



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EXAMINER <i>Maister Wam</i>	DATE CONSIDERED <i>5/12/06</i>
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						<table border="1"> <tr> <th>YES</th> <th>NO</th> </tr> </table>	YES	NO
YES	NO							
MEW	0 297 654 A1	01/04/1989	EP					
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new		Smorchkova, I. et al., "AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy," <i>Journal of Applied Physics</i> , Vol. 90, No. 10, pp. 5196-5201 (November 15, 2001)
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